



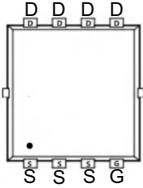
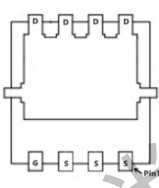


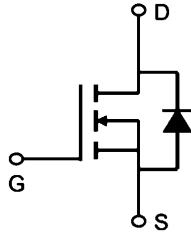
# TM60N04DF

# N-Channel Enhancement Mosfet

|  |  |
|--|--|
| <p><b>General Description</b></p> <ul style="list-style-type: none"> <li>• Low <math>R_{DS(ON)}</math></li> <li>• RoHS and Halogen-Free Compliant</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>• Load switch</li> <li>• PWM</li> </ul> | <p><b>General Features</b></p> <p><math>V_{DS} = 40V</math> <math>I_D = 60A</math></p> <p><math>R_{DS(ON)} = 5.7m\Omega(\text{typ.}) @ V_{GS} = 10V</math></p> <p>100% UIS Tested<br/>100% <math>R_g</math> Tested</p> |
|--|--|



DF:PDFN3x3-8L

Marking:60N04

**Absolute Maximum Ratings** ( $T_c = 25^\circ C$  unless otherwise noted)

| Symbol                    | Parameter                                | Rating     | Units      |
|---------------------------|--|------------|------------|
| $V_{DS}$                  | Drain-Source Voltage                     | 40         | V          |
| $V_{GS}$                  | Gate-Source Voltage                      | $\pm 20$   | V          |
| $I_D @ T_c = 25^\circ C$  | Continuous Drain Current, $V_{GS} @ 10V$ | 60         | A          |
| $I_D @ T_c = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 30         | A          |
| $I_{DM}$                  | Pulsed Drain Current                     | 160        | A          |
| $E_{AS}$                  | Single pulsed avalanche energy           | 81         | mJ         |
| $P_D @ T_c = 25^\circ C$  | Total Power Dissipation <sup>4</sup>     | 21         | W          |
| $T_{STG}$                 | Storage Temperature Range                | -55 to 175 | $^\circ C$ |
| $T_J$                     | Operating Junction Temperature Range     | -55 to 175 | $^\circ C$ |

**Thermal Data**

| Symbol          | Parameter                           | Typ. | Max. | Unit         |
|-----------------|-------------------------------------|------|------|--------------|
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient | ---  | ---  | $^\circ C/W$ |
| $R_{\theta JC}$ | Thermal Resistance Junction-Case    | ---  | 6    | $^\circ C/W$ |



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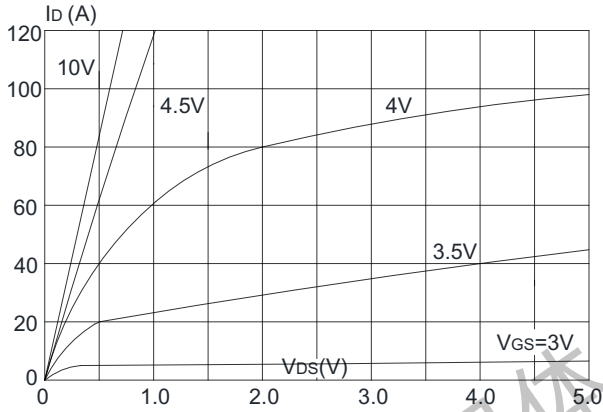
Electrical Characteristics: ( $T_c=25^\circ\text{C}$  unless otherwise noted)

| Symbol                                    | Parameter                          | Conditions                                       | Min | Typ  | Max       | Units         |
|---|------------------------------------|--|-----|------|-----------|---------------|
| <b>Off Characteristics</b>                |                                    |  |     |      |           |               |
| $BV_{DSS}$                                | Drain-Source Breakdown Voltage     | $V_{GS}=0V, I_D=250\ \mu\text{A}$                | 40  | ---  | ---       | V             |
| $I_{DSS}$                                 | Drain-Source Leakage Current       | $V_{GS}=0V, V_{DS}=40V$                          | --- | ---  | 1         | $\mu\text{A}$ |
| $I_{GSS}$                                 | Gate-Source Leakage Current        | $V_{GS}=\pm 20V, V_{DS}=0A$                      | --- | ---  | $\pm 100$ | nA            |
| <b>On Characteristics</b>                 |                                    |  |     |      |           |               |
| $V_{GS(th)}$                              | GATE-Source Threshold Voltage      | $V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$            | 1.2 | 1.6  | 2.0       | V             |
| $R_{DS(on)}$                              | Drain-Source On Resistance         | $V_{GS}=10V, I_D=30A$                            | --- | 5.7  | 7.5       | $m\ \Omega$   |
|   |                                    | $V_{GS}=4.5V, I_D=20A$                           | --- | 10   | 14        |               |
| <b>Dynamic Characteristics</b>            |                                    |  |     |      |           |               |
| $C_{iss}$                                 | Input Capacitance                  | $V_{DS}=20V, V_{GS}=0V, f=1\text{MHz}$           | --- | 2399 | ---       | $\mu\text{F}$ |
| $C_{oss}$                                 | Output Capacitance                 |  | --- | 191  | ---       |               |
| $C_{rss}$                                 | Reverse Transfer Capacitance       |  | --- | 164  | ---       |               |
| <b>Switching Characteristics</b>          |                                    |  |     |      |           |               |
| $t_{d(on)}$                               | Turn-On Delay Time                 | $V_{DD}=20V, V_{GS}=10V, R_G=3\ \Omega, I_D=20A$ | --- | 11   | ---       | ns            |
| $t_r$                                     | Rise Time                          |  | --- | 11   | ---       | ns            |
| $t_{d(off)}$                              | Turn-Off Delay Time                |  | --- | 37   | ---       | ns            |
| $t_f$                                     | Fall Time                          |  | --- | 8    | ---       | ns            |
| $Q_g$                                     | Total Gate Charge                  | $V_{DS}=20V, V_{GS}=10V, I_D=30A$                | --- | 36   | ---       | nC            |
| $Q_{gs}$                                  | Gate-Source Charge                 |  | --- | 5    | ---       | nC            |
| $Q_{gd}$                                  | Gate-Drain "Miller" Charge         |  | --- | 6    | ---       | nC            |
| <b>Drain-Source Diode Characteristics</b> |                                    |  |     |      |           |               |
| $I_S$                                     | Continuous Source Current          |  | --- | ---  | 60        | A             |
| $I_{SM}$                                  | Pulsed Source Current              |  | --- | ---  | 160       | A             |
| $V_{SD}$                                  | Forward on voltage                 | $I_S=30A, V_{GS}=0V$                             | --- | ---  | 1.2       | V             |
| $T_{rr}$                                  | Body Diode Reverse Recovery Time   | $I_F=20A, dI/dt=100A/\mu\text{s}$                | --- | 22   | ---       | nS            |
| $Q_{rr}$                                  | Body Diode Reverse Recovery Charge |  | --- | 11   | ---       | nC            |

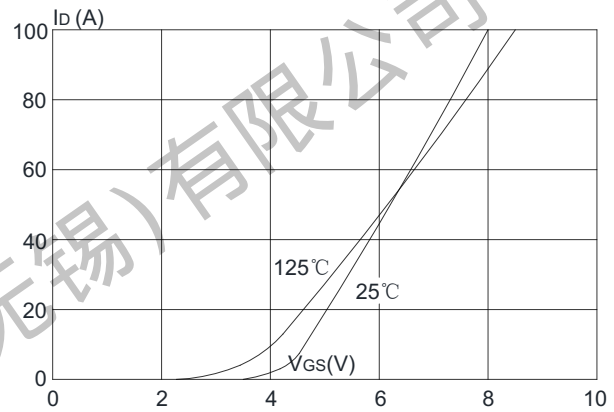
**TM60N04DF**

**N-Channel Enhancement Mosfet**

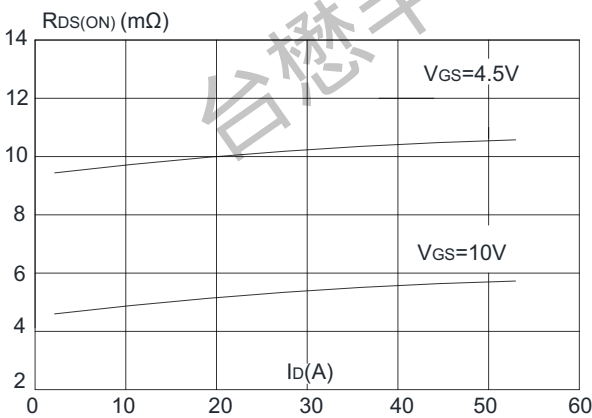
Typical Characteristics: ( $T_c=25^\circ\text{C}$  unless otherwise noted)



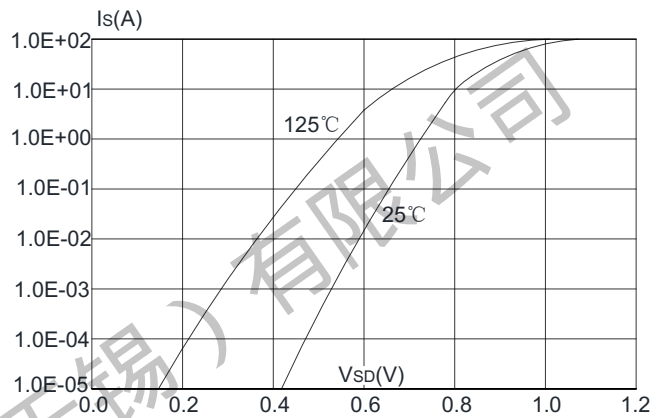
**Figure 1:** Output Characteristics



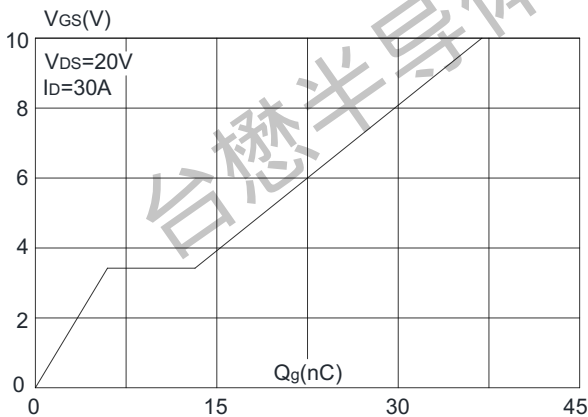
**Figure 2:** Typical Transfer Characteristics



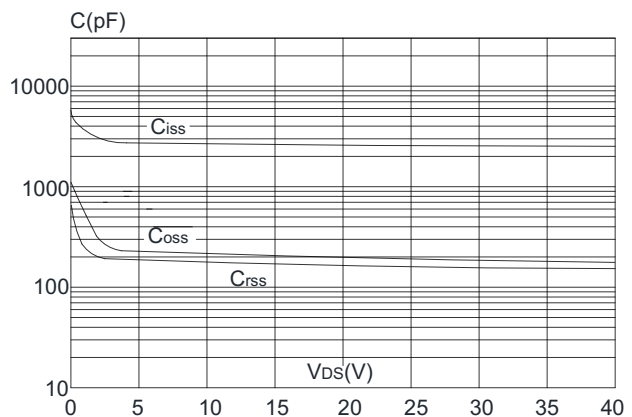
**Figure 3:** On-resistance vs. Drain Current



**Figure 4:** Body Diode Characteristics



**Figure 5:** Gate Charge Characteristics



**Figure 6:** Capacitance Characteristics



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N-Channel Enhancement Mosfet

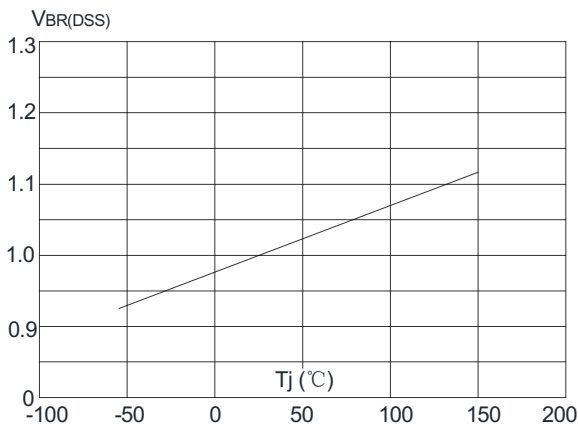


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

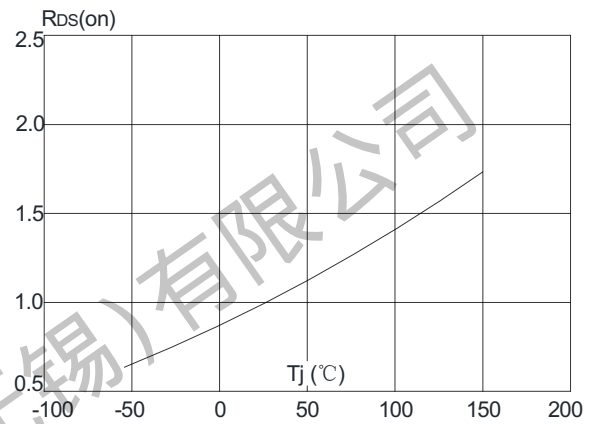


Figure 8: Normalized on Resistance vs. Junction Temperature

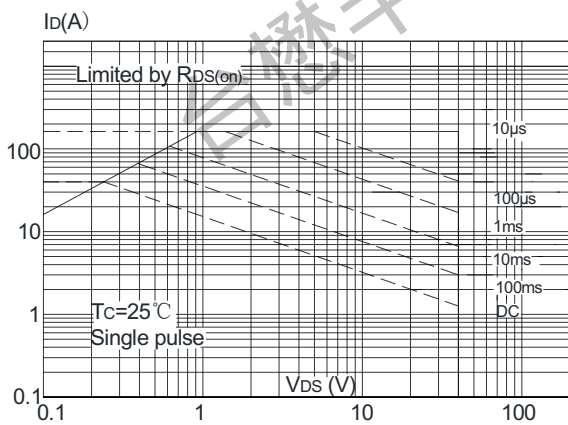


Figure 9: Maximum Safe Operating Area

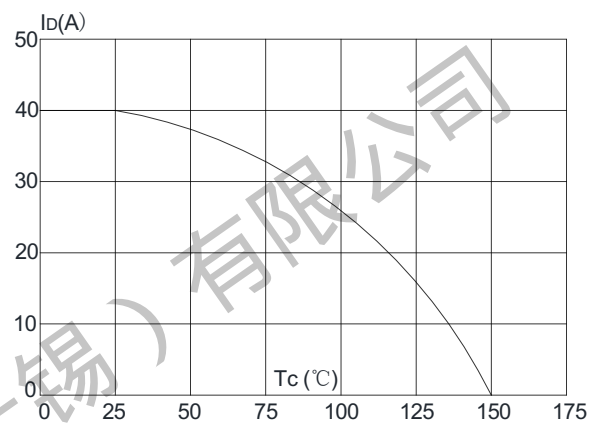


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

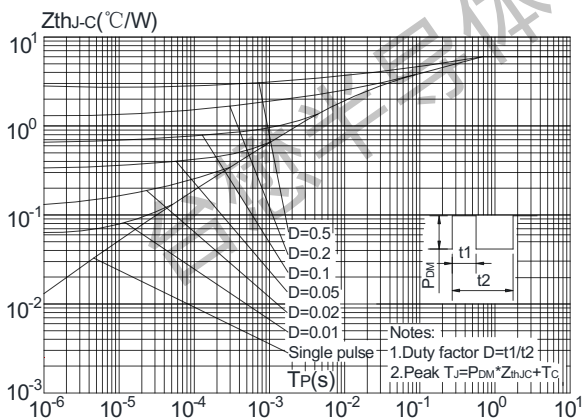


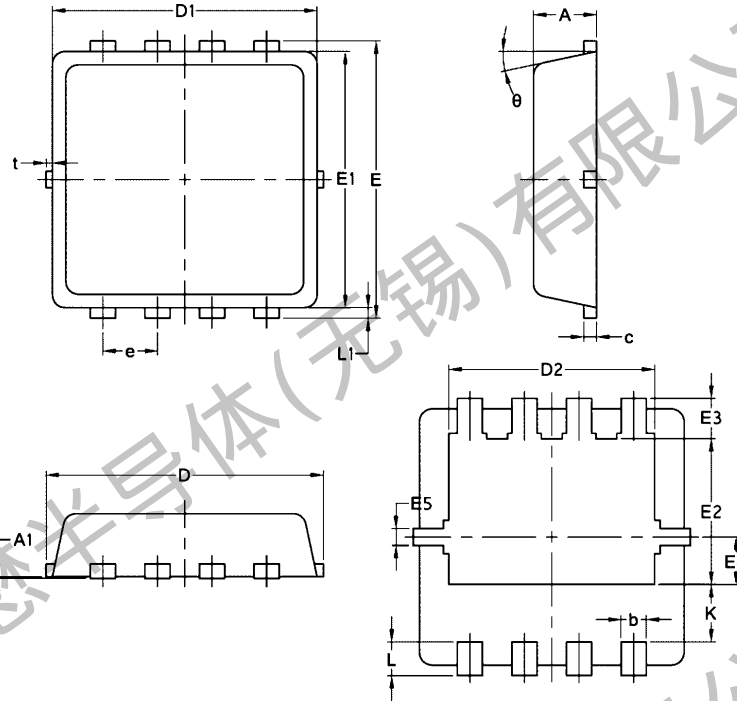
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



**TM60N04DF**

**N-Channel Enhancement Mosfet**

**Package Mechanical Data:DFN3x3-8L**



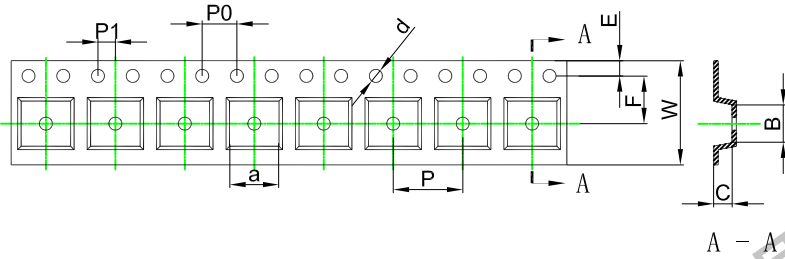
| Symbol | Common |       |      |
|--------|--------|-------|------|
|        | mm     |       |      |
|        | Mim    | Nom   | Max  |
| A      | 0.70   | 0.75  | 0.85 |
| A1     | /      | /     | 0.05 |
| b      | 0.20   | 0.30  | 0.40 |
| c      | 0.10   | 0.152 | 0.25 |
| D      | 3.15   | 3.30  | 3.45 |
| D1     | 3.00   | 3.15  | 3.25 |
| D2     | 2.29   | 2.45  | 2.65 |
| E      | 3.15   | 3.30  | 3.45 |
| E1     | 2.90   | 3.05  | 3.20 |
| E2     | 1.54   | 1.74  | 1.94 |
| E3     | 0.28   | 0.48  | 0.65 |
| E4     | 0.37   | 0.57  | 0.77 |
| E5     | 0.10   | 0.20  | 0.30 |
| e      | 0.60   | 0.65  | 0.70 |
| K      | 0.59   | 0.69  | 0.89 |
| L      | 0.30   | 0.40  | 0.50 |
| L1     | 0.06   | 0.125 | 0.20 |
| t      | 0      | 0.075 | 0.13 |
| Φ      | 10     | 12    | 14   |



TM60N04DF

N-Channel Enhancement Mosfet

PDFN3x3-8L Embossed Carrier Tape



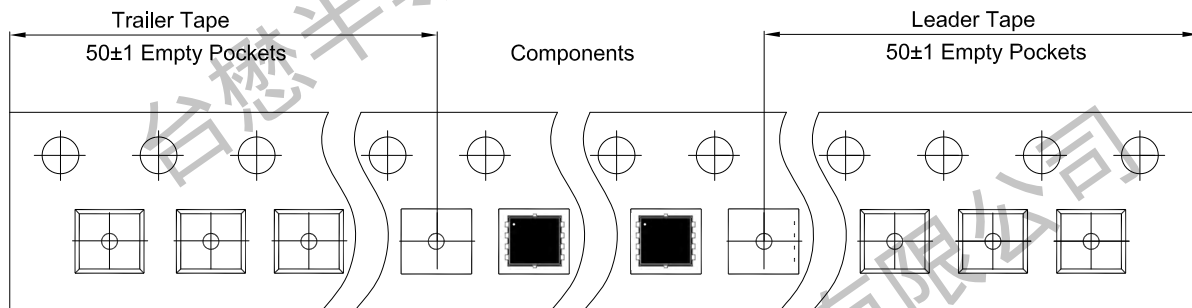
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

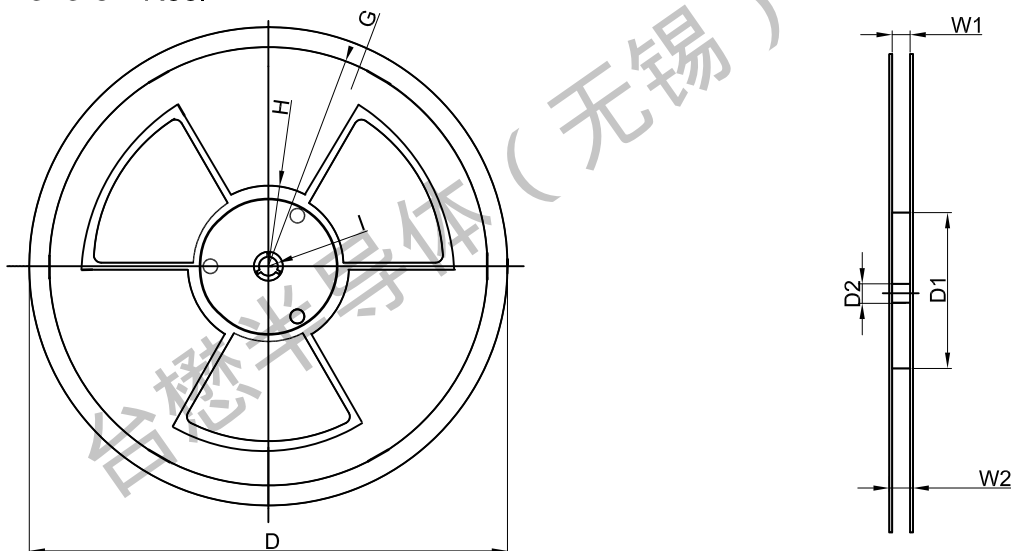
ALL DIM IN mm

| Dimensions are in millimeter |      |      |      |       |      |      |      |      |      |       |
|------------------------------|------|------|------|-------|------|------|------|------|------|-------|
| Pkg type                     | a    | B    | C    | d     | E    | F    | P0   | P    | P1   | W     |
| PDFN3x3-8L                   | 6.40 | 5.40 | 2.10 | Ø1.50 | 1.75 | 5.50 | 4.00 | 8.00 | 2.00 | 12.00 |

PDFN3x3-8L Tape Leader and Trailer



PDFN3x3-8L Reel



| Dimensions are in millimeter |         |        |       |         |        |       |       |       |
|------------------------------|---------|--------|-------|---------|--------|-------|-------|-------|
| Reel Option                  | D       | D1     | D2    | G       | H      | I     | W1    | W2    |
| 13" Dia                      | Ø330.00 | 100.00 | 13.00 | R135.00 | R55.00 | R6.50 | 12.00 | 14.00 |

| REEL      | Reel Size | Box        | Box Size(mm) | Carton     | Carton Size(mm) | G.W.(kg) |
|-----------|-----------|------------|--------------|------------|-----------------|----------|
| 5,000 pcs | 13 inch   | 10,000 pcs | 370×355×52   | 50,000 pcs | 400×360×368     |          |



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Revision history:

| Date       | Rev   | Description | Page |
|------------|-------|-------------|------|
| 2023.05.10 | 23.05 | Original    |      |